600V Super-junction Power MOSFET

Description

600V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs，designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

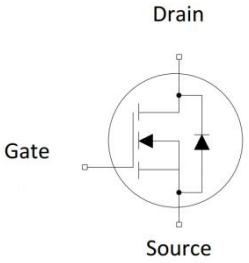
Features

- Very low FOM RDS(on)×Qg
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-220F



RoHS

Device Marking and Package Information

Device	Package	Marking
TPA60R160D	TO-220F	60R160D

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$	0.16	Ω
$Q_{g,typ}$	36	nC
I_D	20	A
$I_{D,pulse}$	60	A
E_{OSS} @ 400V	4.67	μJ

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted				
Parameter		**Symbol**	**Value**	**Unit**
Continuous Drain Current	T_C = 25ºC	I_D	20	A
	T_C = 100ºC		12	
Pulsed Drain Current (note1)		$I_{D,pulse}$	60	A
Gate-Source Voltage		V_{GSS}	±30	V
Single Pulse Avalanche Energy (note2)		E_{AS}	450	mJ
Avalanche Current		I_{AR}	9.5	A
MOSFET dv/dt Ruggedness, V_{DS} = 0...650V		dv/dt	50	V/ns
Power Dissipation For TO-220F		P_D	34	W
Continuous Diode Forward Current		I_S	20	A
Diode Pulsed Current (note1)		$I_{S,pulse}$	60	
Reverse Diode dv/dt (note3)		dv/dt	5	A/us
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	ºC

Thermal Resistance For TO-220F			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	3.7	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Electrical Characteristics T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 600V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 10A	--	0.13	0.16	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	2216	--	pF
Output Capacitance	C_{oss}		--	90	--	
Reverse Transfer Capacitance	C_{rss}		--	6	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 20A, V_{GS} = 10V	--	36	--	nC
Gate-Source Charge	Q_{gs}		--	10	--	
Gate-Drain Charge	Q_{gd}		--	12	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 20A, R_G = 25Ω	--	45	--	ns
Turn-on Rise Time	t_r		--	68	--	
Turn-off Delay Time	$t_{d(off)}$		--	130	--	
Turn-off Fall Time	t_f		--	9	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 20A, V_{GS} = 0V	--	0.95	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_S=3A, di_F/dt = 100A/μs	--	450	--	ns
Reverse Recovery Charge	Q_{rr}		--	8.1	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	3.4	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

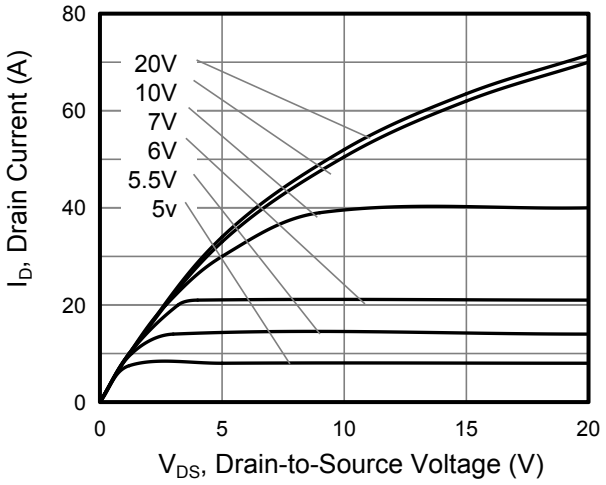


Figure 2. Transfer Characteristics

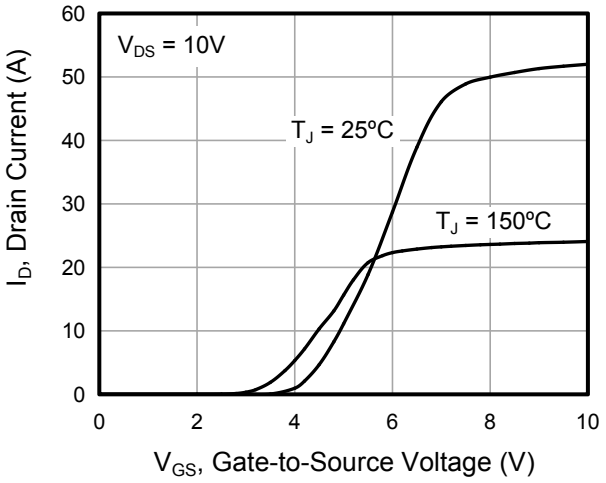


Figure 3. On-Resistance vs. Drain Current

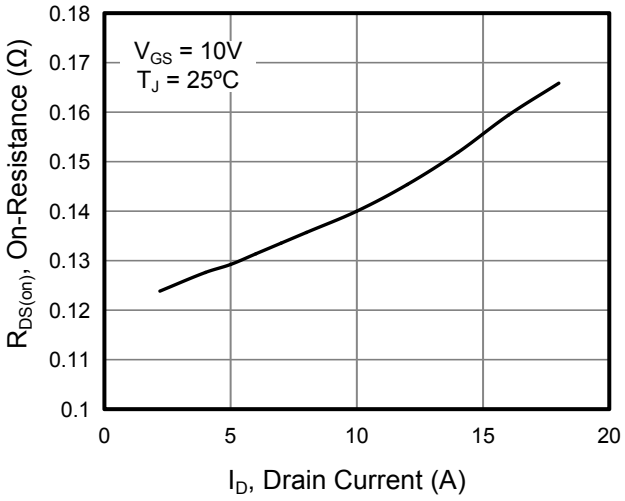


Figure 4. Capacitance

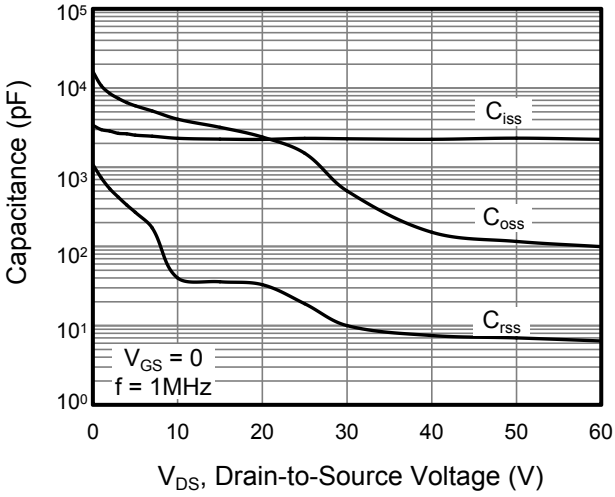


Figure 5. Gate Charge

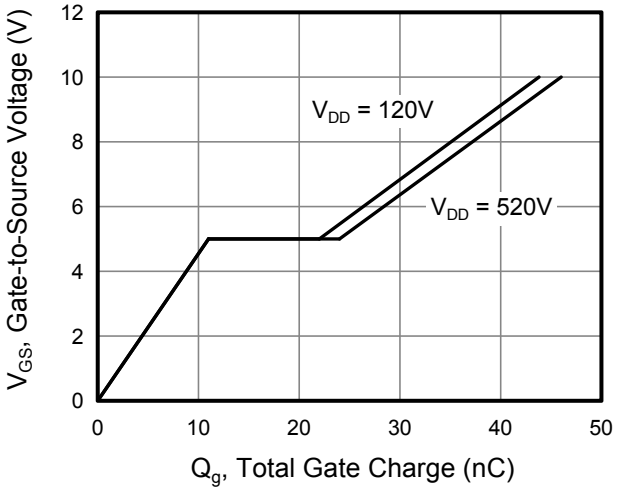


Figure 6. Body Diode Forward Voltage

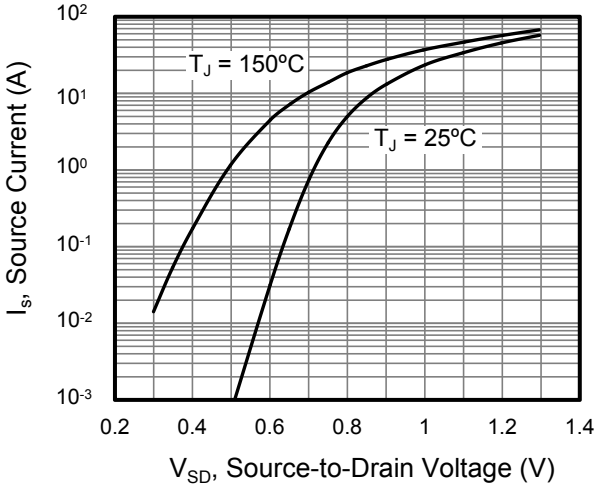


Figure 7. On-Resistance vs. Temperature

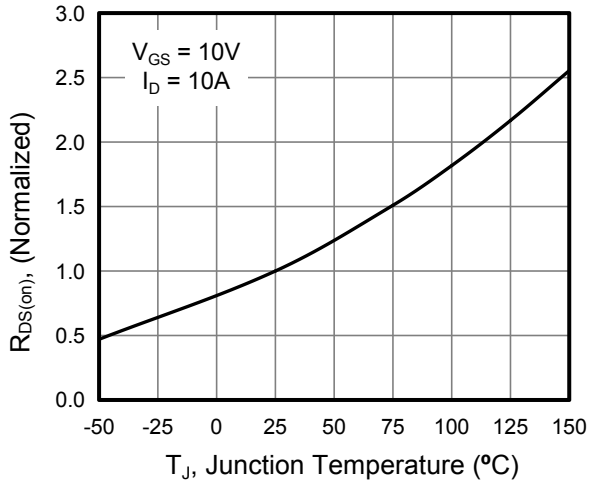


Figure 8. Breakdown voltage vs. Junction Temperature

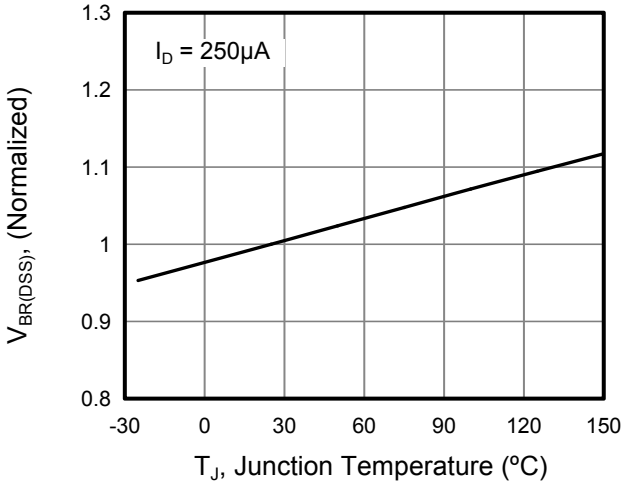


Figure 9. Transient Thermal Impedance For TO-220F

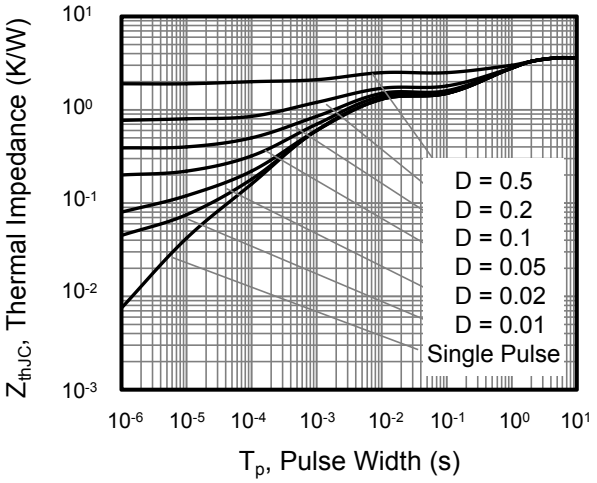


Figure 10. Safe Operation Area For TO-220F

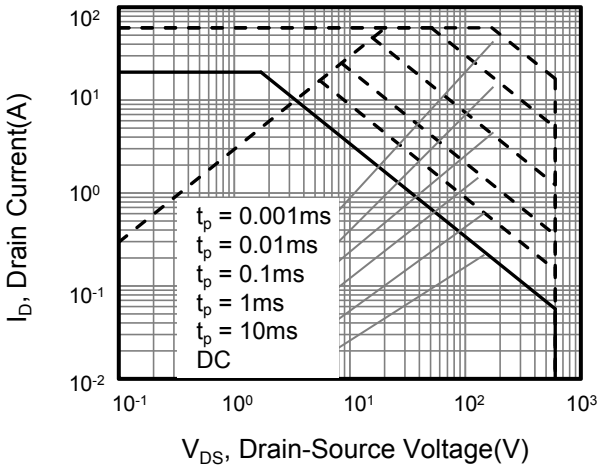


Figure 11. Typ. Coss Stored Energy

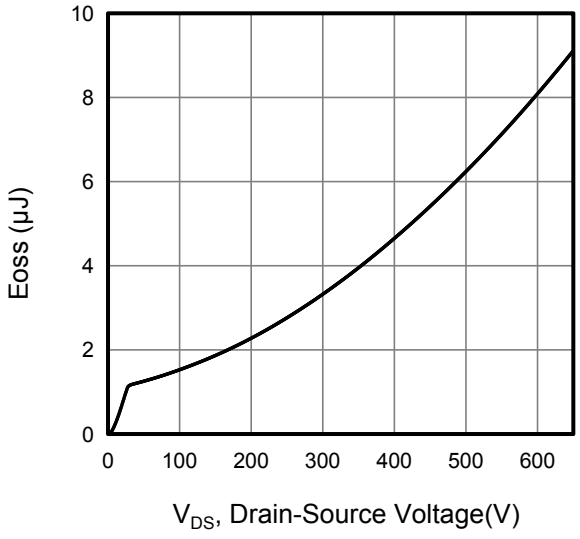


Figure A：Gate Charge Test Circuit and Waveform

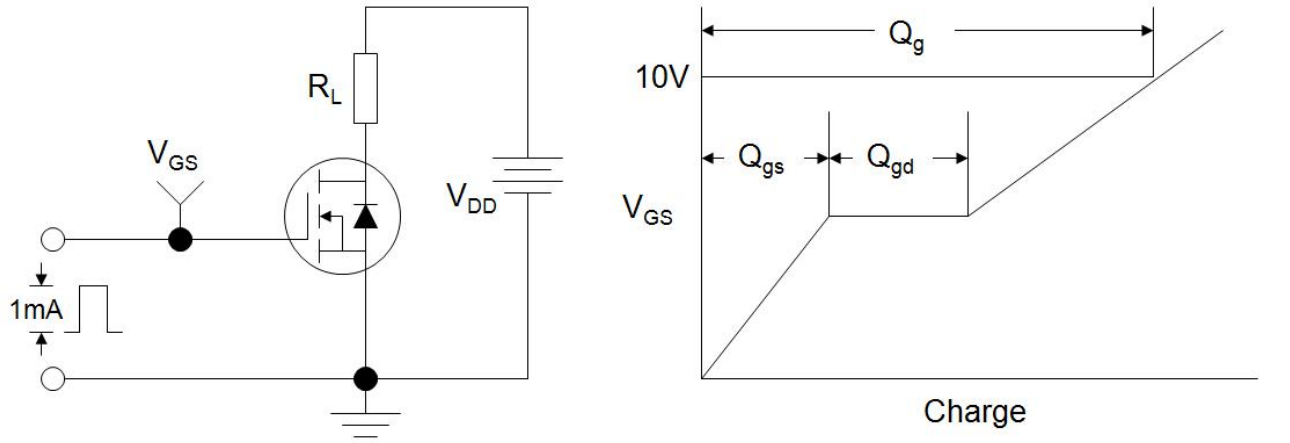


Figure B：Resistive Switching Test Circuit and Waveform

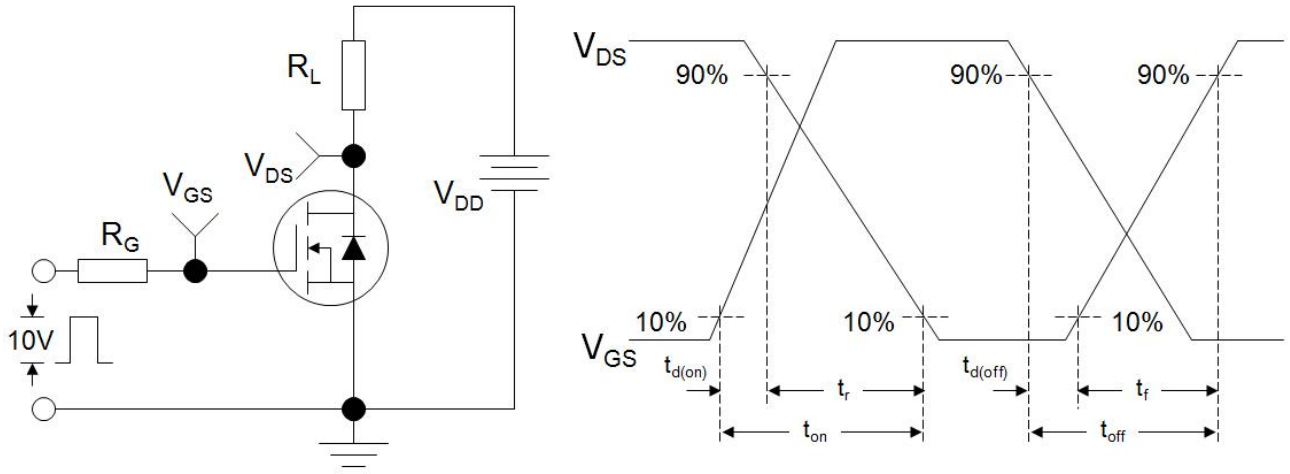
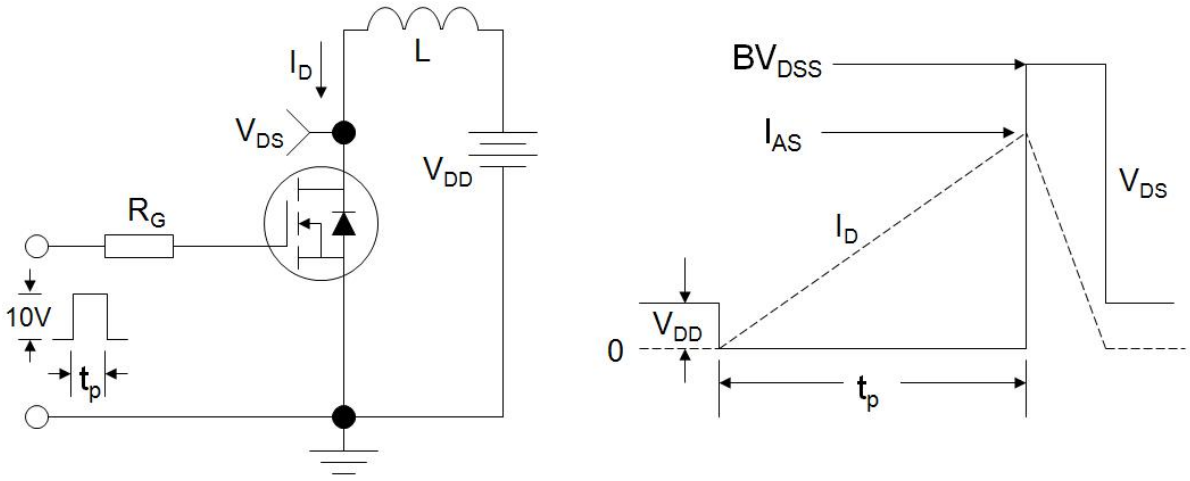
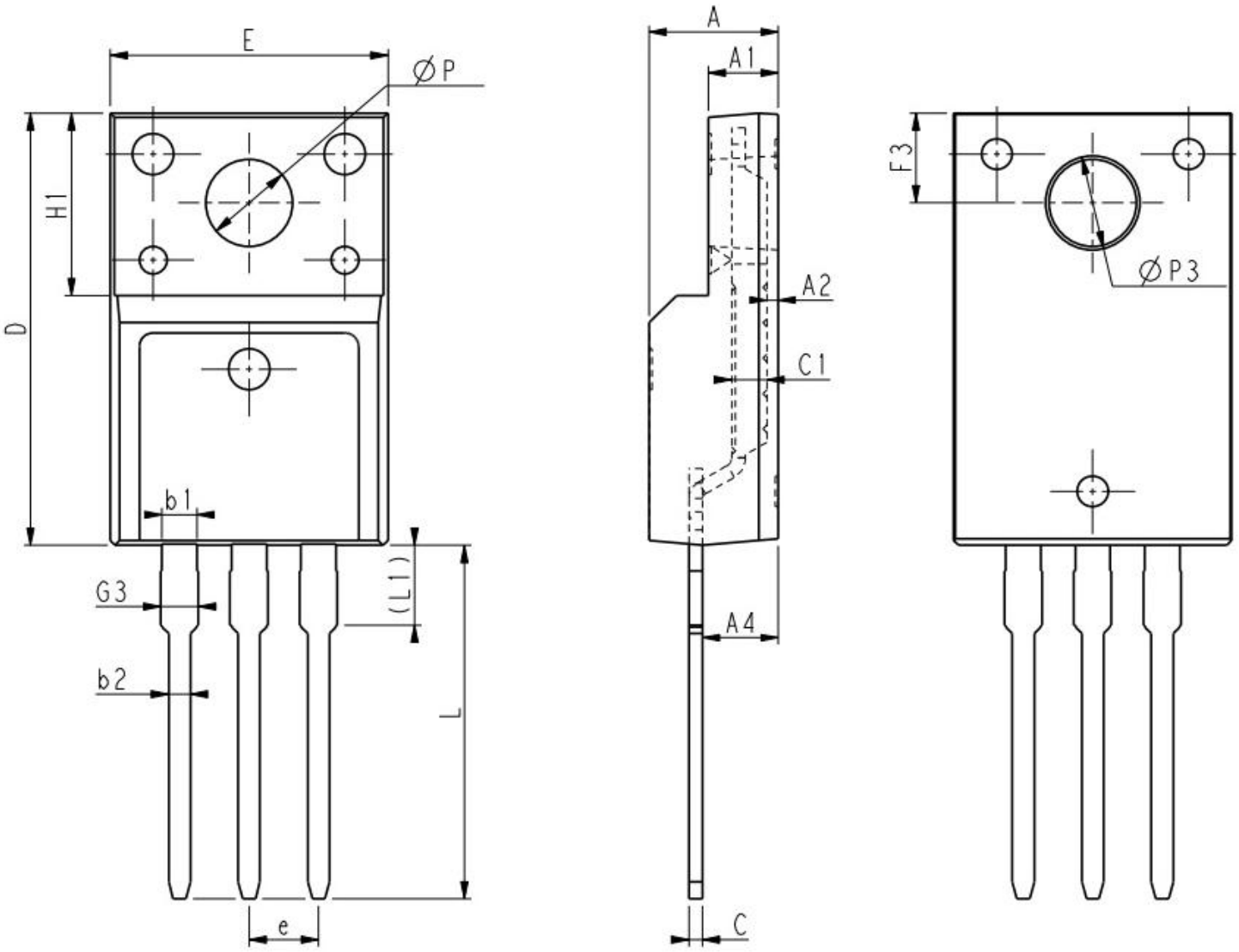


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



TO-220F（封装厂 H）



Unit:mm			
Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
ΦP	3.03	3.18	3.38
ΦP3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

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